

HHQ Series RF High Q Multilayer Chip Ceramic Capacitor

1. Capacitor characteristics and applications

1.1 Characteristics

- Size specifications are standardized and suitable for surface mount components in hybrid integrated circuits or printed circuits
- High Q value, low ESR, high reliability
- Low loss, high capacitance stability, high operating frequency
- Suitable for high-frequency circuits, VHF-microwave bands, RF and amplification circuits in various equipment

1.2 Main performance indicators

- Temperature coefficient: C0G: $0 \pm 30 \text{ ppm}/^\circ\text{C}$
- Capacitance drift: no more than $\pm 0.2\%$ or $\pm 0.05 \text{ pF}$, whichever is larger.
- Quality factor (Q value): greater than 2,000 at a frequency of 1mHz/1kHz
- Insulation resistance: $> 100000 \text{ m}\Omega$ at 20°C
- Operating temperature: $-55 \sim 125^\circ\text{C}$

2. Product model naming

How to order

<u>HHQ</u>	<u>1111</u>	<u>C0G</u>	<u>1R0</u>	<u>B</u>	<u>501</u>	<u>N</u>	<u>T</u>
Type	Size	Dielectric	Capacitance unit: (pF)	Tolerance	Rated voltage	Termination	Packaging style
HHQ series RF high Q capacitor	0402 2525 0603 3838 0805 6243 0505 7676 1111	C0G: $+30 \text{ ppm}/^\circ\text{C}$	The first two digits are significant figures, and the last digit is the power of 10	A: $\pm 0.05 \text{ pF}$ B: $+0.10 \text{ pF}$ C: $+0.25 \text{ pF}$ D: $+0.50 \text{ pF}$ F: $+1.0\%$ G: $+2.0\%$ J: $+5.0\%$ K: $\pm 10.0\%$	The first two digits are significant figures, and the last digit is the power of 10	N: Leading-out Terminal: Ag/Ni/Sn Terminal: Z: Leading-out Ag/Ni/Sn/Pb E: Non-magnetic Terminal M: Microstrip, A: Axial tape RW: Radial wire, RN: Non-magnetic radial wire	T: Tape & reel C: Cut Tray B: Bulk